

Excellent Integrated System Limited

Stocking Distributor

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ON Semiconductor NTUD3170NZT5G

For any questions, you can email us directly: sales@integrated-circuit.com



NTUD3170NZ

Small Signal MOSFET

20 V, 220 mA, Dual N-Channel, 1.0 mm x 1.0 mm SOT-963 Package

Features

- Dual N-Channel MOSFET
- Offers a Low R_{DS(ON)} Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics
- This is a Pb-Free Device

Applications

- General Purpose Interfacing Switch
- Optimized for Power Management in Ultra Portable Equipment
- Analog Switch

MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise specified)

Para	Symbol	Value	Unit			
Drain-to-Source Voltage			V _{DSS}	20	V	
Gate-to-Source Voltage			V _{GS}	±8	V	
Continuous Drain	Steady	$T_A = 25^{\circ}C$		220	mA	
Current (Note 1)	State	$T_A = 85^{\circ}C$	I_{D}	160		
	t ≤ 5 s	$T_A = 25^{\circ}C$		280		
Power Dissipation	Steady State	T _A = 25°C	P _D	125		
(Note 1)					mW	
	t ≤ 5 s			200		
Pulsed Drain Current	I _{DM}	800	mA			
Operating Junction and Storage Temperature			T _J , T _{STG}	–55 to 150	°C	
Source Current (Body Diode) (Note 2)			IS	200	mA	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

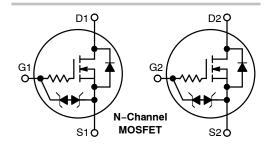
- Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.
- 2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%



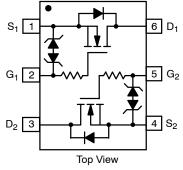
ON Semiconductor®

http://onsemi.com

V _{(BR)DSS}	R _{DS(ON)} MAX	I _D Max	
	1.5 Ω @ 4.5 V		
20 V	2.0 Ω @ 2.5 V	0.22 A	
	3.0 Ω @ 1.8 V		
	4.5 Ω @ 1.5 V		



PINOUT: SOT-963







3 = Specific Device Code

M = Date Code ■ = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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Datasheet of NTUD3170NZT5G - MOSFET 2N-CH 20V 0.22A SOT-963

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THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 3)	$R_{ hetaJA}$	1000	°C/W
Junction-to-Ambient - t = 5 s (Note 3)	т⊎JA	600	0/11

^{3.} Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	on	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•	•		•			
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20			V
Zero Gate Voltage Drain Current			T _J = 25°C			50	nA
	I _{DSS}	$V_{GS} = 0 \text{ V}, V_{DS} = 5 \text{ V}$	T _J = 85°C			200	
		V _{GS} = 0 V, V _{DS} = 16 V	T _J = 25°C			100	nA
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5.0 \text{ V}$				±100	nA
ON CHARACTERISTICS (Note 4)	•	•		•	•		
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = 2$	250 μA	0.4		1.0	V
Drain-to-Source On Resistance		$V_{GS} = 4.5 \text{ V}, I_D = 100 \text{ M}$	$V_{GS} = 4.5 \text{ V}, I_D = 100 \text{ mA}$		0.75	1.5	
		V _{GS} = 2.5 V, I _D = 50 mA			1.0	2.0	Ω
	R _{DS(ON)}	V _{GS} = 1.8 V, I _D = 20 mA			1.4	3.0	
		V _{GS} = 1.5 V, I _D = 10 mA			1.8	4.5	
		V _{GS} = 1.2 V, I _D = 1.0 mA			2.8		
Forward Transconductance	9FS	V _{DS} = 5.0 V, I _D = 125 mA			0.48		S
Source-Drain Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 mA			0.6	1.0	V
CAPACITANCES							
Input Capacitance	C _{ISS}				12.5		
Output Capacitance	C _{OSS}	f = 1.0 MHz, V _{GS} = 0 V V _{DS} = 15 V			3.6		pF
Reverse Transfer Capacitance	C _{RSS}				2.6		
SWITCHING CHARACTERISTICS, V _{GS} =	4.5 V (Note 4)						
Turn-On Delay Time	t _{d(ON)}	V_{GS} = 4.5 V, V_{DD} = 10 V, I_{D} = 200 mA, R_{G} = 2.0 Ω			16.5		
Rise Time	t _r				25.5		ns
Turn-Off Delay Time	t _{d(OFF)}				142		
Fall Time	t _f				80		

^{4.} Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

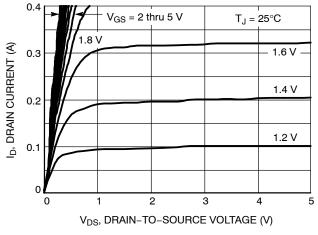
Device	Package	Shipping [†]		
NTUD3170NZT5G	SOT-963 (Pb-Free)	8000 / Tape & Reel		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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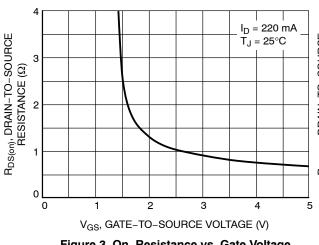
TYPICAL CHARACTERISTICS



 $T_J = -55^{\circ}C$ $V_{DS} \ge 5 V$ $T_J = 25^{\circ}C$ T_J = 125°C _D, DRAIN CURRENT (A) 0.3 0.2 0.1 0 0 2 3 V_{GS}, GATE-TO-SOURCE VOLTAGE (V)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



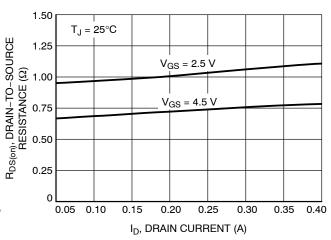
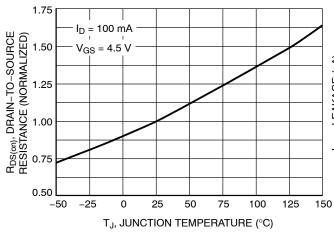


Figure 3. On-Resistance vs. Gate Voltage

Figure 4. On-Resistance vs. Drain Current and **Gate Voltage**



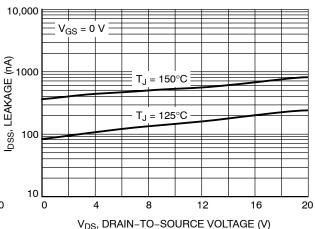


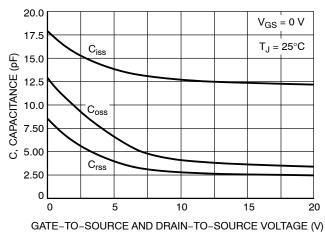
Figure 5. On-Resistance Variation with **Temperature**

Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS



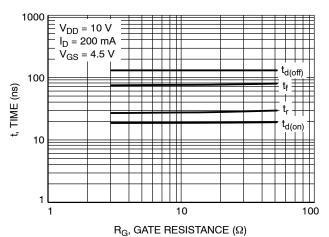


Figure 7. Capacitance Variation

Figure 8. Resistive Switching Time Variation vs. Gate Resistance

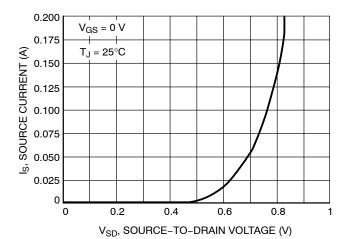


Figure 9. Diode Forward Voltage vs. Current



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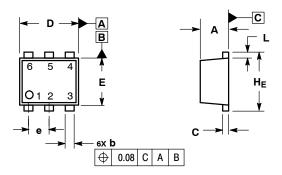
Datasheet of NTUD3170NZT5G - MOSFET 2N-CH 20V 0.22A SOT-963

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PACKAGE DIMENSIONS

SOT-963 CASE 527AD-01 ISSUE D

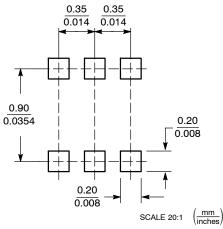


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.34	0.37	0.40			
b	0.10	0.15	0.20	0.004	0.006	0.008
С	0.07	0.12	0.17	0.003	0.005	0.007
О	0.95	1.00	1.05	0.037	0.039	0.041
E	0.75	0.80	0.85	0.03	0.032	0.034
е		0.35 BSC		(0.014 BS	C
٦	0.05	0.10	0.15	0.002	0.004	0.006
HE	0.95	1.00	1.05	0.037	0.039	0.041

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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